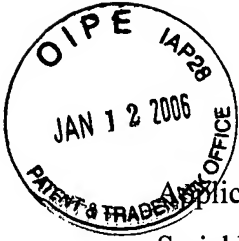


Serial No. 10/725,325



IFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Fwu-Iuan Hshieh et al.

Serial No.: 10/725,325

Filed: 12/01/2003

Title: Method Of Making a Trench MOSFET Device With Improved On-Resistance

Art Unit: 2811

Examiner: Loke, Steven Ho Yin

Docket No.: GS 152 D1

VIA FACSIMILE 571-273-8300

Mail Stop Amendment

Commissioner for Patents

PO Box 1450

Alexandria, VA 22313-1450

AMENDMENT

Sir:

Responsive to the outstanding non-final Office Action dated September 8, 2005 in the above-identified patent application, the time for response extended one month, up to and including Monday, January 9, 2006, please enter the following amendments and remarks. In addition, any deficiencies may be charged to deposit account No. 50-1047.

Certificate of Mail

I hereby certify that this document and any document referenced herein is being deposited with the US Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to

Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450 on January 9, 2006

Karin L. Williams, Reg. No. 36,721

(Printed Name of Person Mailing Correspondence)

Karin L. Williams
(Signature)